

FS50ASJ-03F

High-Speed Switching Use Nch Power MOS FET

REJ03G0238-0200 Rev.2.00 Dec 19, 2008

Features

• Drive Voltage: 4V

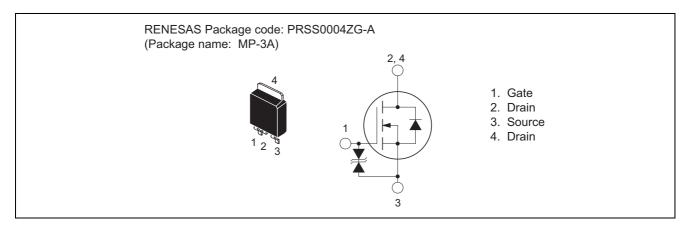
 $\bullet \quad V_{DSS}:30\;V$

• $r_{DS(ON) (max)}$: 12.2 m Ω

• I_D: 50 A

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 50 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25 \, ^{\circ}C)$

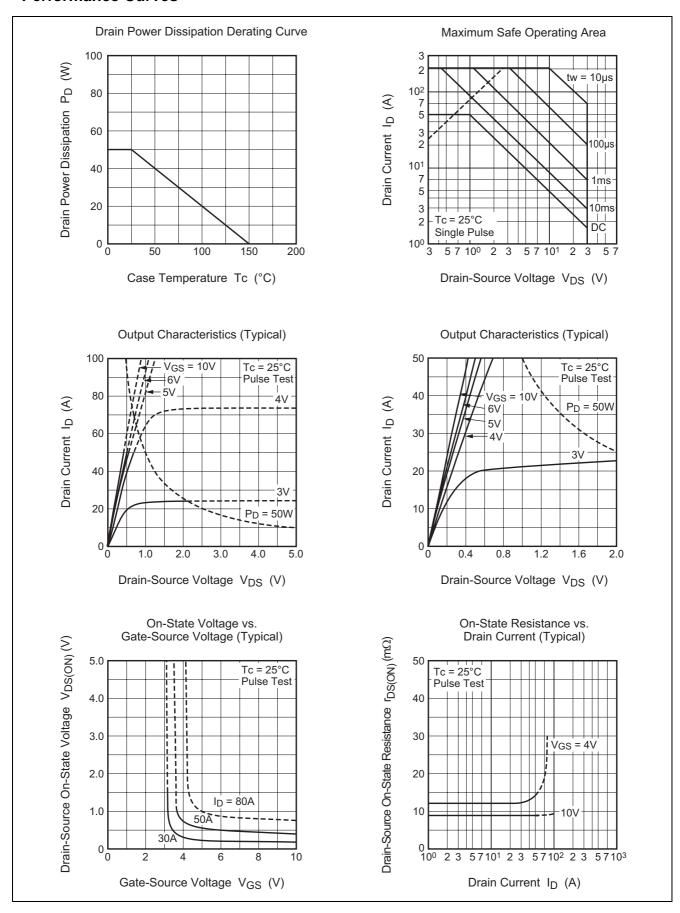
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	30	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	$V_{DS} = 0 V$
Drain current	I _D	50	А	
Drain current (Pulse)	I _{DM}	200	А	
Avalanche current (Pulse)	I _{DA}	50	А	L = 6 μH
Source current	Is	50	А	
Source current (Pulse)	I _{SM}	200	А	
Maximum power dissipation	P _D	50	W	
Channel temperature	Tch	- 55 to + 150	°C	
Storage temperature	Tstg	- 55 to + 150	°C	
Mass	_	0.32	g	Typical value

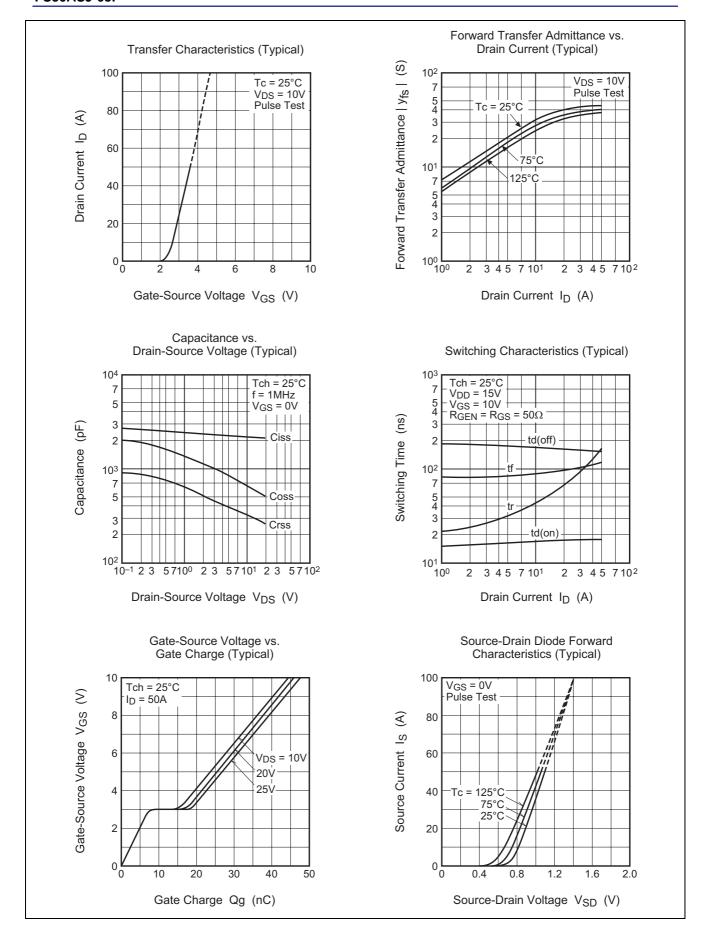
Electrical Characteristics

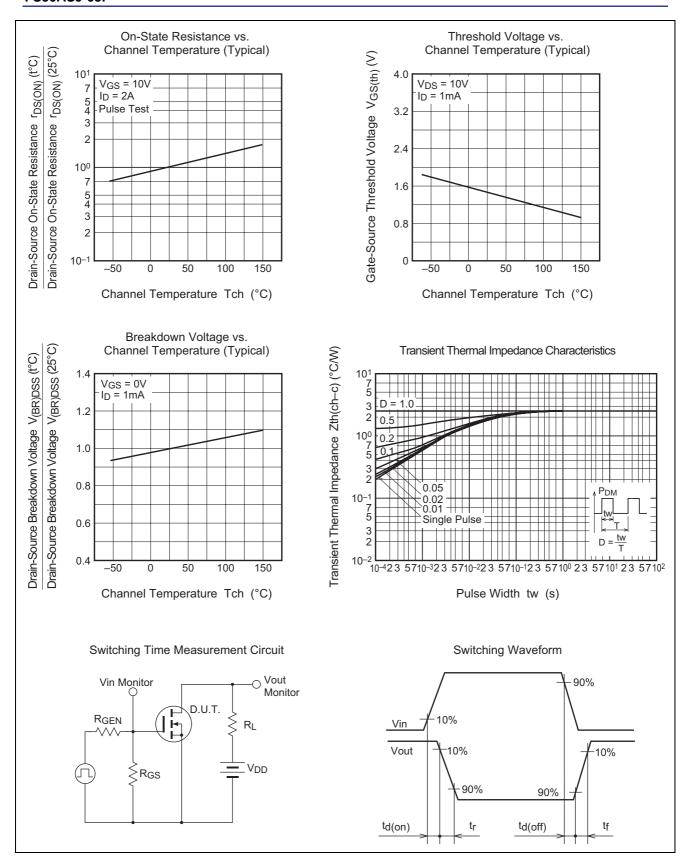
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V _{(BR)DSS}	30	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	V _{(BR)GSS}	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0 \ V$
Drain-source leakage current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	9.2	12.2	mΩ	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	13	19	mΩ	I _D = 25 A, V _{GS} = 4 V
Drain-source on-state voltage	V _{DS(ON)}	_	0.23	0.31	V	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}$
Forward transfer admittance	y _{fs}	_	45	_	S	$I_D = 25 \text{ A}, V_{DS} = 10 \text{ V}$
Input capacitance	Ciss	_	2100	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1MHz
Output capacitance	Coss	_	690	_	pF	
Reverse transfer capacitance	Crss	_	340	_	pF	
Turn-on delay time	t _{d(on)}	_	16	_	ns	$V_{DD} = 15 \text{ V}, I_{D} = 25 \text{ A},$ $V_{GS} = 10 \text{ V},$ $R_{GEN} = R_{GS} = 50 \Omega$
Rise time	t _r	_	90	_	ns	
Turn-off delay time	t _{d(off)}	_	130	_	ns	
Fall time	t _f	_	85	_	ns	
Source-drain voltage	V _{SD}	_	1.0	1.5	V	I _S = 25 A, V _{GS} = 0 V
Thermal resistance	Rth(ch-c)	_	_	2.5	°C/W	Channel to case
Diode reverse recovery time	t _{rr}	_	50	_	ns	$I_S = 25 \text{ A}, \text{ dis/dt} = -50 \text{ A/}\mu\text{s}$

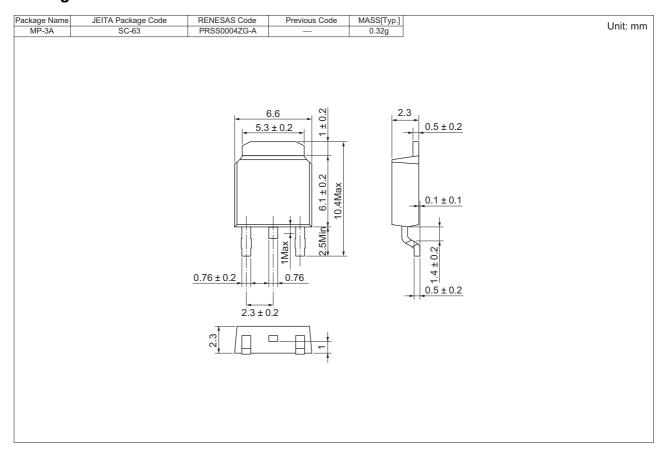
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS50ASJ-03F-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS50ASJ-03F

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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